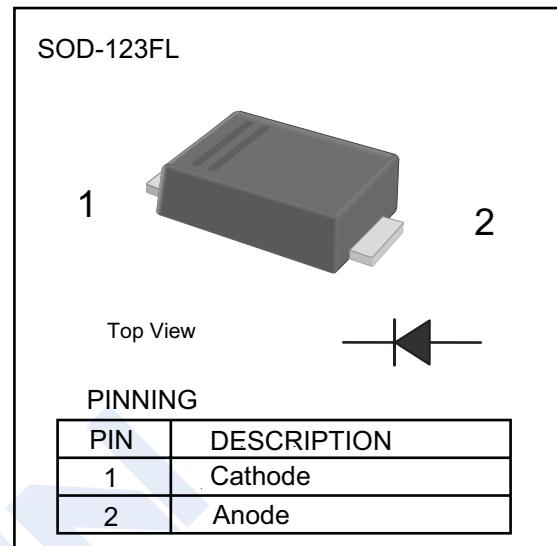


Schottky Diodes

1N5817FL ~ 1N5819FL

■ Features

- Low power loss, high efficiency
- High current capability
- Low forward voltage drop
- High Surge Capability



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	1N5817FL	1N5818FL	1N5819FL	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	20	30	40	V
RMS Voltage	V _{RMS}	14	21	28	
DC Blocking Voltage	V _{DC}	20	30	40	
Forward Voltage @ I _F =1A	V _F	0.45	0.55	0.6	
Forward Voltage @ I _F =3.1A		0.75	0.875	0.9	
Average Forward Rectified Current @ T _L =90°C	I _{FAV}	1			A
Non-Repetitive Peak Forward Surge Current @8.3ms	I _{FSM}	25			
Reverse Voltage Leakage Current Ta = 25°C Ta = 100°C	I _R	1			mA
		10			
Typical Junction Capacitance	C _J	110			pF
Junction Temperature	T _J	125			°C
Storage Temperature range	T _{stg}	-55 to 125			

■ Marking

NO.	1N5817FL	1N5818FL	1N5819FL
Marking	SJ	SK	SL

Schottky Diodes

1N5817FL ~ 1N5819FL

■ Typical Characteristics

Fig.1 Forward Current Derating Curve

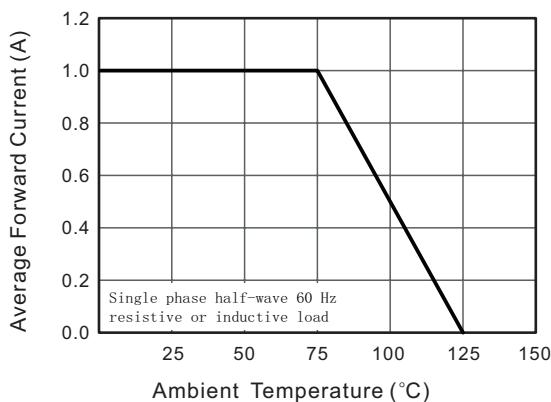


Fig.3 Typical Forward Characteristic

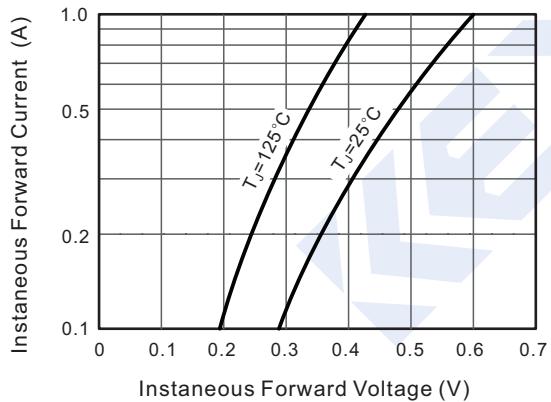


Fig.5 Maximum Non-Repetitive Peak Forward Surge Current

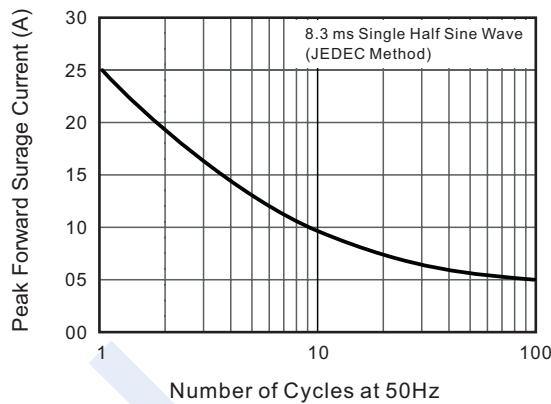


Fig.2 Typical Reverse Characteristics

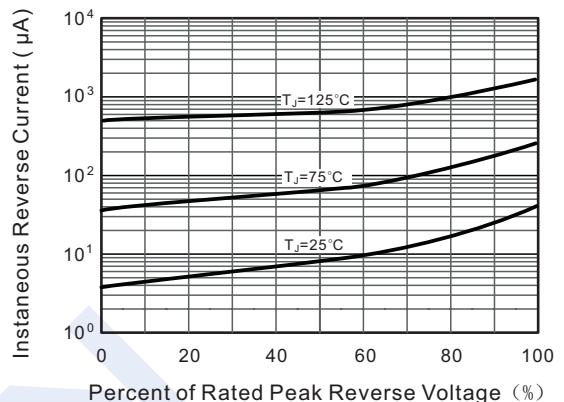


Fig.4 Typical Junction Capacitance

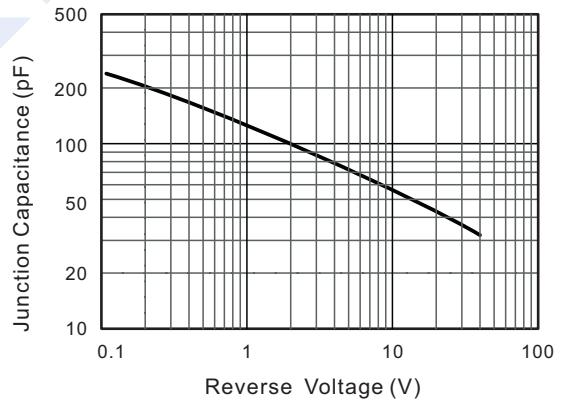
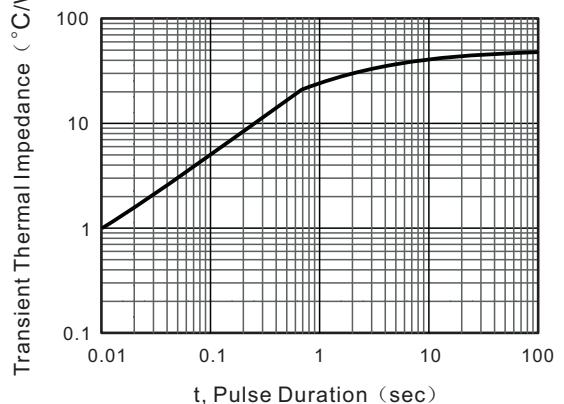


Fig.6-Typical Transient Thermal Impedance



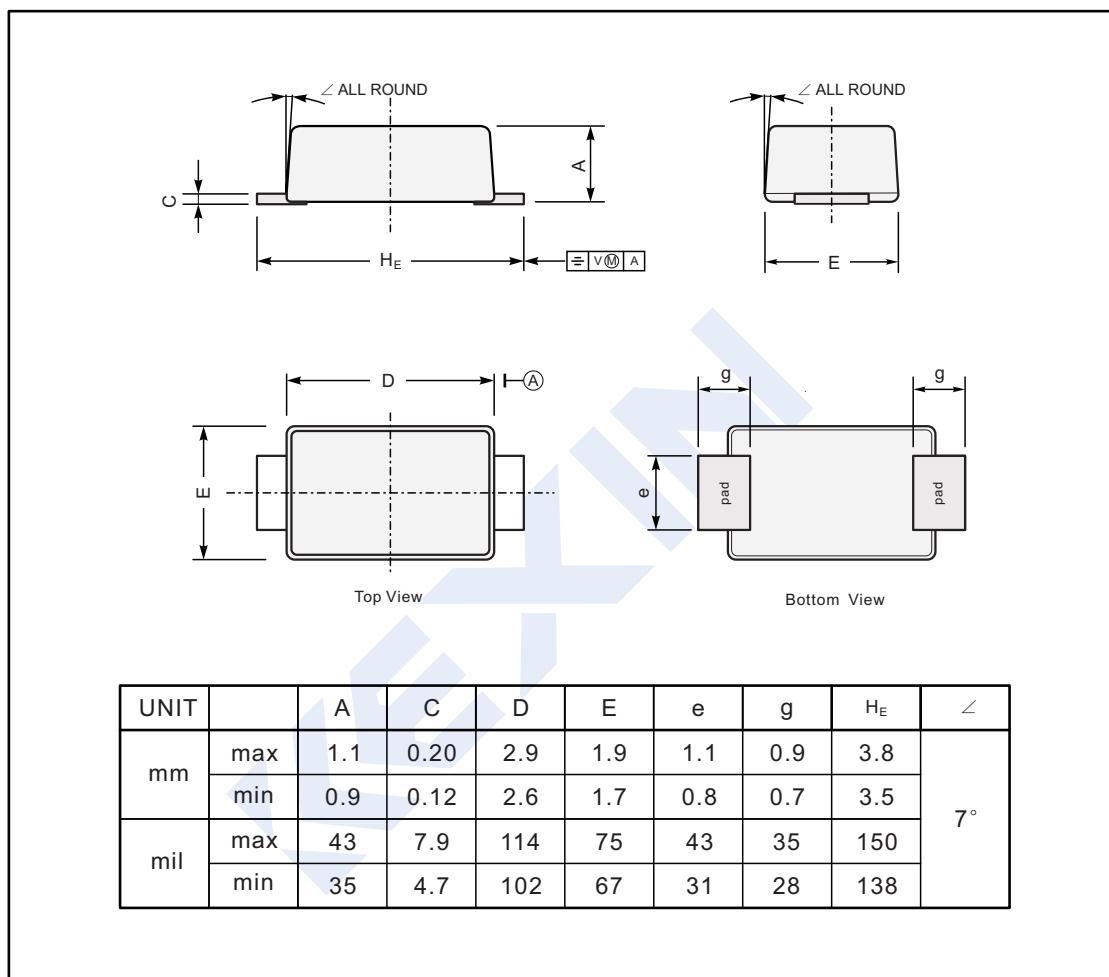
Schottky Diodes

1N5817FL ~ 1N5819FL

■ Package Outline Dimensions

Plastic surface mounted package; 2 leads

SOD-123FL



■ The Recommended Mounting Pad Size

